Hybrid-Type Capacitive Pressure Sensor

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This paper describes a capacitive pressure sensor of the hybrid type which contains CMOS integrated circuits to detect the capacitance. Relative pressure can be measured with this sensor. The sensor is 4.5×3.4 mm square and $400 \, \mu$ m thick. In order to simplify the fabrication process of the sensor, the diaphragm thickness was controlled by means of a monitor groove. The measured sensitivity of the sensor is about 70 ppm/mmHg. The thermal zero shift and the thermal sensitivity shift in the range 5 to $45\,^{\circ}$ C are 0.1%F.S./ $^{\circ}$ C and less than 0.21%F.S./ $^{\circ}$ C, respectively. The interface circuit is fabricated with $10 \, \mu$ m CMOS technology. The output frequency from the C-F converter can be detected with only two lead wires.

1. Introduction

A silicon diaphragm pressure sensor transforms applied pressure into an electrical signal, based on a piezoresistive effect^(1,2) or a capacitive effect,^(3,4) using a deformable silicon diaphragm. As a single-crystalline silicon has superior elastic characteristics, virtually no creep or hysteresis occurs, even if static pressure is applied to the diaphragm. Because of this reliability, silicon diaphragm pressure sensors have been widely used in such application fields as medical instrumentation and automobile engine control, as well as for industrial purposes. These sensors must have sufficient sensitivity, good stability, high signal-to-noise (S/N) ratio, and so